APPLICATION INFORMATION

2.4 GHz low noise amplifier with the BFG480W





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ABSTRACT

- · Description of the product
 - The BFG480W is one of the Philips double polysilicon wideband transistors of the BFG400 series.
- · Application area
 - Low voltage high frequency wireless applications.
- · Presented application
 - A low noise amplifier for 2.4 GHz applications such as wireless local area network and wireless local loop.
- Main results
 - At a frequency of 2.4 GHz, the amplifier has an insertion power gain of approximately 9.5 dB, a noise figure of approximately 3 dB, and a third order intercept point of approximately 17 dBm (measured at input).

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INTRODUCTION

With the Philips double polysilicon wideband transistor BFG480W, it is possible to design Low Noise Amplifiers (LNAs) for high frequency applications with a low current and a low supply voltage. These amplifiers are well suited for the new generation low voltage high frequency wireless applications. One feature of the BFG480W is that it has a good linearity performance. Therefore the BFG480W is well suited for LNAs with high linearity demands, such as Code Division Multiple Access (CDMA) systems. This application note gives an example of a 2.4 GHz LNA with the BFG480W. Because this LNA design has a high third order intercept value of 17 dBm (measured at input), it can be used for Wireless Local Area Network (WLAN) front-end and Wireless Local Loop (WLL) applications.

CIRCUIT DESCRIPTION

The following initial conditions apply for the amplifier design:

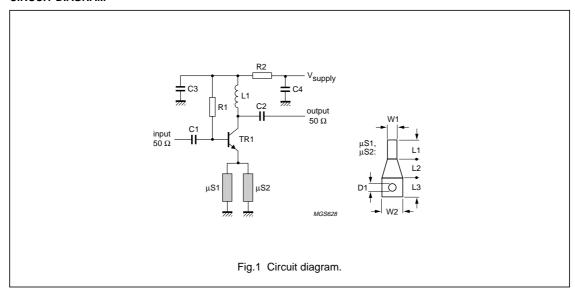
- $V_{supply} \approx 3.6 \text{ V}$
- V_{CF} = 2 V
- I_C = 40 mA
- f = 2.4 GHz.

The circuit is designed to show the following performance:

- $|s_{21}|^2 \approx 9 \, dB$
- VSWR_{IN} < 2
- VSWR_{OUT} < 2
- NF ≤ 3.5 dB
- IP3_i > 15 dBm.

The output matching is realised with an LC combination. Also an extra emitter inductance (micro stripline) is used on both emitter-leads to improve the matching and the noise figure.

CIRCUIT DIAGRAM



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COMPONENT LIST

Table 1 Component list for the 2.4 GHz LNA

COMPONENT	VALUE	UNIT	SIZE, MANUFACTURER	PURPOSE, COMMENT	
TR1	BFG480W		SOT343R Philips	RF transistor	
R1	2.7	kΩ	0603 Philips	collector to base bias	
R2	39	Ω	0603 Philips	collector series bias; levelling h _{FE} spread	
C1	5.6	pF	0603 Philips	input match (base coupling)	
C2	3.3	pF	0603 Philips	output match (collector coupling)	
C3	5.6	pF	0603 Philips	2.4 GHz short (L1 to ground)	
C4	1	nF	0603 Philips	RF collector bias decoupling	
L1	150	nH	0805CS Coilcraft	output match	
μS1	see Table 2			emitter induction: micro stripline and via-hole	
μS2	see Table 2			emitter induction: micro stripline and via-hole	
PCB	FR4			$\epsilon_r \approx 4.6$, d = 0.5 mm	

Table 2 Dimensions of the micro striplines $\mu S1$ and $\mu S2$ (see Fig.1)

DIMENSION	VALUE	UNIT	DESCRIPTION	
L1	1.0	mm	length micro stripline; $Z_0 \approx 48 \Omega$	
L2	1.0	mm	length interconnect micro stripline and via-hole area	
L3	1.0	mm	length via-hole area	
W1	0.5	mm	width micro stripline	
W2	1.0	mm	width via-hole area	
D1	0.4	mm	diameter of via-hole	

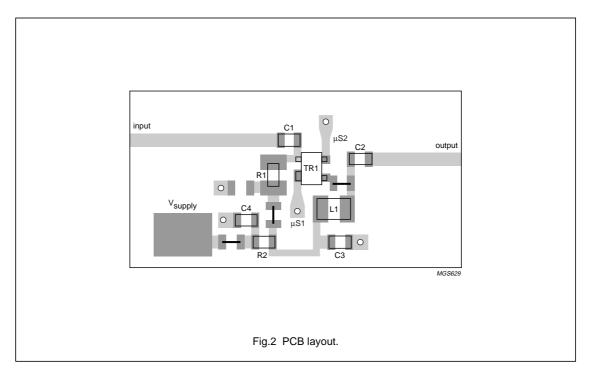
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BOARD LAYOUT

Short-circuit wires are used to adapt an existing printed-circuit board, which was developed for low noise applications. The layout has been designed with the Hewlett Packard Microwave Design System (HP-MDS).



MEASUREMENTS

The measurements have been done under the following conditions (unless otherwise specified):

- Supply voltage 3.6 V
- Supply current 40 mA
- Frequency 2.4 GHz.

Table 3 Measuring results of the 2.4 GHz LNA

SYMBOL	PARAMETER	CONDITION	VALUE	UNIT
s ₂₁ ²	insertion power gain		9.6	dB
VSWR _{IN}	input voltage standing wave ratio		1.6	
VSWR _{OUT}	output voltage standing wave ratio		1.6	
NF	noise figure		3.0	dB
IP3 _i	third order intercept point	$P_i = -10 \text{ dBm}$; $\Delta f = 200 \text{ kHz}$	17	dBm

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